

2SK2577(Tentative)

Silicon N-Channel Power F-MOS

■ Features

- Avalanche energy capability guaranteed
- High-speed switching
- Low ON-resistance
- No secondary breakdown
- Low-voltage drive

■ Applications

- Non-contact relay
- Solenoid drive
- Motor drive
- Control equipment
- Switching mode regulator

■ Absolute Maximum Ratings (T_c = 25°C)

Parameter	Symbol	Rating	Unit	
Drain-Source breakdown voltage	V _{DSS}	100	V	
Gate-Source voltage	V _{GSS}	±20	V	
Drain current	DC	I _D	±30	A
	Pulse	I _{DP}	±60	A
Avalanche energy capability	EAS *	20	mJ	
Allowable power dissipation	T _c = 25°C	P _D	45	W
	T _a = 25°C		2	
Channel temperature	T _{ch}	150	°C	
Storage temperature	T _{stg}	-55 to +150	°C	

* L= 0.1mH, I_L= 20A, 1 pulse

■ Electrical Characteristics (T_c = 25°C)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Drain-Source cut-off current	I _{DSS}	V _{DS} = 80V, V _{GS} = 0			10	μA
Gate-Source leakage current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0			±1	μA
Drain-Source breakdown voltage	V _{DSS}	I _D =1mA, V _{GS} = 0	100			V
Gate threshold voltage	V _{th}	V _{DS} =10V, I _D =1mA	1		2.5	V
Drain-Source ON-resistance	R _{DS(on)1}	V _{GS} =10V, I _D =15A		48	70	mΩ
	R _{DS(on)2}	V _{GS} = 4V, I _D =10A		56	85	mΩ
Forward transadmittance	Y _{fs}	V _{DS} =10V, I _D =15A	12	20		S
Diode forward voltage	V _{DSF}	I _{DR} = 30A, V _{GS} = 0			-1.7	V
Input capacitance	C _{iss}	V _{DS} =10V, V _{GS} = 0, f=1MHz		3350		pF
Output capacitance	C _{oss}			800		pF
Feedback capacitance	C _{rss}			230		pF
Turn-on time	t _{on}	V _{DD} = 30V, I _D =15A V _{GS} =10V, R _L =2Ω		130		ns
Fall time	t _f			190		ns
Turn-off time (delay time)	t _{d(off)}			700		ns
Channel-Case heat resistance	R _{th(ch-c)}				2.78	°C/W
Channel-Atmosphere heat resistance	R _{th(ch-a)}				62.5	°C/W



